

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
30 June 2005 (30.06.2005)

PCT

(10) International Publication Number
WO 2005/059971 A2

(51) International Patent Classification⁷: **H01L 21/00**

(21) International Application Number:
PCT/IB2004/052778

(22) International Filing Date:
13 December 2004 (13.12.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0329002.0 15 December 2003 (15.12.2003) GB
0426413.1 2 December 2004 (02.12.2004) GB

(71) Applicant (for all designated States except US): **KONINKLIJKE PHILIPS ELECTRONICS N.V.** [NL/NL];
Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(72) Inventor; and

(75) Inventor/Applicant (for US only): **DEANE, Steven, C.**
[GB/GB]; c/o Philips Intellectual Property & Standards
(GB).

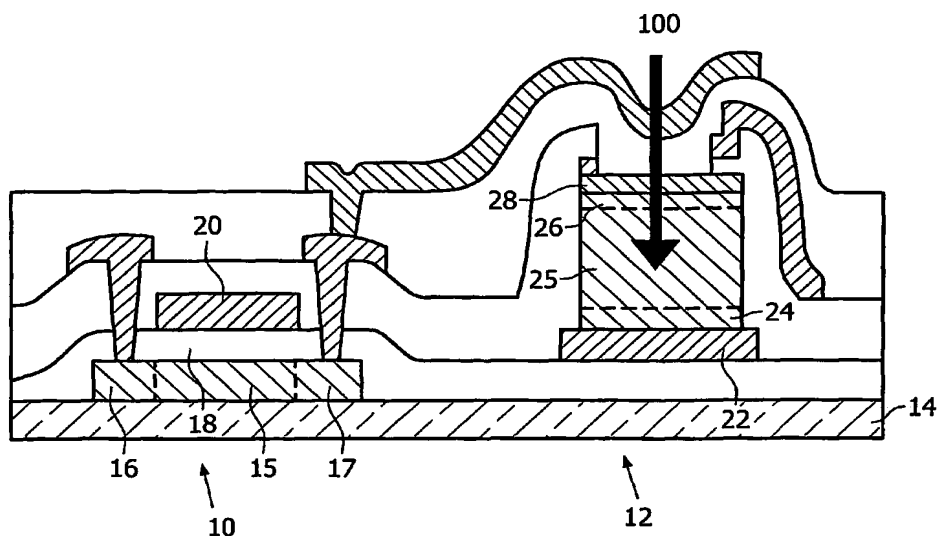
(74) Agents: **WILLIAMSON, Paul, L.** et al.; c/o Philips Intellectual Property & Standards, Cross Oak Lane, Redhill Surrey RH1 5HA (GB).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: **ACTIVE MATRIX PIXEL DEVICE WITH PHOTO SENSOR**



(57) Abstract: An active matrix pixel device is provided, for example an electroluminescent display device, the device comprising circuitry supported by a substrate and including a polysilicon TFT (10) and an amorphous silicon thin film PIN diode (12). Polysilicon islands are formed before an amorphous silicon layer is deposited for the PIN diode. This avoids the exposure of the amorphous silicon to high temperature processing. The TFT comprises doped source/drain regions (16a, 17a), one of which (17a) may also provide the n-type or p-type doped region for the diode. Advantageously, the requirement to provide a separate doped region for the photodiode is removed, thereby saving processing costs. A second TFT (10b) having a doped source/drain region (16b, 17b) of the opposite conductivity type may provide the other doped region (16b) for the diode, wherein the intrinsic region (25) is disposed laterally between the two TFTs, overlying each of the respective polysilicon islands.

**Declaration under Rule 4.17:**

- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE,

BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

Published:

- without international search report and to be republished upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.